NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI TPV7025** is Designed for Television Band IV & V Applications up to 860 MHz.

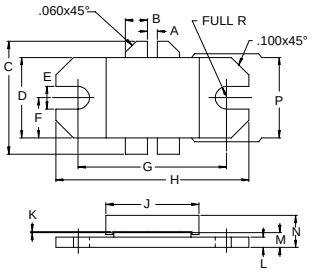
FEATURES:

- Common Emitter
- P_G = 9.0 dB at 25 W/860 MHz
- ***Omnigold***™ Metalization System

MAXIMUM RATINGS

I_C	8.0 A
V_{CBO}	45 V
V_{CEO}	28 V
V_{EBO}	4.0 V
P_{DISS}	86 W @ T_C = 70 °C
T_J	-50 °C to +200 °C
T_{STG}	-50 °C to +200 °C
θ_{JC}	1.5 °C/W

PACKAGE STYLE .450 BAL FLG(A)



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.055 / 1.40	
B	.120 / 3.05	.130 / 3.30
C		.785 / 19.94
D	.455 / 11.56	.465 / 11.81
E	.120 / 3.05	.130 / 3.30
F	.230 / 5.84	
G	.838 / 21.28	.850 / 21.59
H	1.095 / 27.81	1.105 / 28.07
J	.525 / 13.34	.535 / 13.59
K	.002 / 0.05	.005 / 0.15
L	.055 / 1.40	.065 / 1.65
M	.080 . 2.03	.095 / 2.41
N		.195 / 4.95
P	.445 / 11.30	.455 / 11.56

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	I_C = 20 mA	45			V
BV_{CEO}	I_C = 120 mA	28			V
BV_{EBO}	I_E = 20 mA	4.0			V
h_{FE}	V_{CE} = 20 V I_C = 1.0 A	10		60	---
C_{OB}	V_{CB} = 28 V f = 1.0 MHz	64		80	pF
P_G	V_{CE} = 25 V I_C = 3.2 A f = 860 MHz	9.0		10.5	dB
IMD_1	P_{OUT} = 25 W			-45	dBc